

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Lutze et al.

Title: Methods for Identifying Non-Volatile Memory Elements with Poor Threshold Slope of Weak Transconductance

Application No.: 10/665,685 Filing Date: September 17, 2003

Examiner: Unknown Group Art Unit: Unknown

Docket No.: SNDK.301US0 Conf. No.: Unknown

Certificate of Mailing Under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on 12/10/03

Signature

Quillen Bower

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

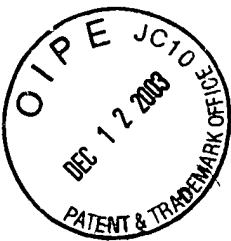
Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicant(s) call(s) the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application.

Copies of the documents listed on the accompanying Form PTO-1449 are enclosed.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

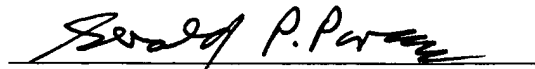
SNDK.301US0

Serial No.: 10/665,685



This information disclosure statement is submitted under 37 C.F.R. § 1.97(b) and consequently no fee should be required. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664. This form is being submitted in duplicate.

Respectfully submitted,



Gerald P. Parsons
Reg. No. 24,486

December 10, 2003

Date

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U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.			Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				SNDK.301US0			10/665,685	
				Applicant(s)			Conf. No.	
				Lutze et al.			Unknown	
				Filing Date			Group	
				September 17, 2003			Unknown	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

U.S. Published Patent Application Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
		Park et al., "Degradation of Thin Tunnel Gate Oxide Under Constant Fowler-Nordheim Current Stress for a Flash Eeprom," <i>IEEE Transactions on Electron Devices</i> , Vol. 45, No. 6, June 1998, pp. 1361-1368.
		Lee et al., "Endurance Characteristics and Degradation Mechanism of Polysilicon Thin Film Transistor EEPROMs with Electron Cyclotron Resonance N ₂ O-Plasma Gate Oxide," <i>Jpn. J. Appl. Phys.</i> , Vol. 38, 1999, pp. 2215-2218.

Examiner	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.